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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
9	☐	☑	US 5605853 A	19970225	9	Method of making a semiconductor device having	438/238	438/258; 438/586;
10	☐	☑	US 5506158 A	19960409	8	BiCMOS process with surface channel PMOS transistor	438/202	257/370; 257/379;
11	☐	☑	US 5489547 A	19960206	13	Method of fabricating semiconductor device having	438/238	148/DIG.136; 148/DIG.146;
12	☐	☑	US 5356826 A	19941018	11	Method of manufacturing semiconductor device	438/238	148/DIG.136; 438/253;
13	☐	☑	US 5187122 A	19930216	16	Process for fabricating an integrated circuit using	438/238	148/DIG.19; 257/532;
14	☐	☑	US 5013678 A	19910507	6	Method of making an integrated circuit	438/384	257/380; 438/238;
15	☐	☑	US 4419812 A	19831213	14	Method of fabricating an integrated circuit voltage	438/238	257/296; 257/379;
16	☐	☑	US 4416049 A	19831122	9	Semiconductor integrated circuit with vertical	438/238	257/380; 257/538;
17	☐	☑	US 4367580 A	19830111	6	Process for making polysilicon resistors	438/238	257/316; 257/380;
18	☐	☑	US 4208781 A	19800624	14	Semiconductor integrated circuit with implanted	438/238	29/610.1; 438/297;

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1	☐	☑	US 6069036 A	20000530	10	Method of fabricating semiconductor device	438/238	438/250; 438/382
2	☐	☑	US 5953599 A	19990914	9	Method for forming low-voltage CMOS transistors	438/199	438/210; 438/238;
3	☐	☑	US 5866451 A	19990202	9	Method of making a semiconductor device having	438/241	438/200; 438/210;
4	☐	☑	US 5837592 A	19981117	10	Method for stabilizing polysilicon resistors	438/382	438/238; 438/385;
5	☐	☑	US 5780333 A	19980714	6	Method of fabricating an analog semiconductor device	438/238	438/250; 438/253;
6	☐	☑	US 5716863 A	19980210	12	Method of manufacturing semiconductor device having	438/238	148/DIG.163; 438/275;
7	☐	☑	US 5706164 A	19980106	13	Method of fabricating high density integrated circuits,	361/321.4	257/296; 257/300;
8	☐	☑	US 5618749 A	19970408	18	Method of forming a semiconductor device having	438/384	148/DIG.136; 148/DIG.14;
9	☐	☑	US 5605853 A	19970225	9	Method of making a semiconductor device having	438/238	438/258; 438/586;
10	☐	☑	US 5506158 A	19960409	8	BiCMOS process with surface channel PMOS transistor	438/202	257/370; 257/379;
11	☐	☑	US 5489547 A	19960206	13	Method of fabricating semiconductor device having	438/238	148/DIG.136; 148/DIG.146;

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1	☐	☑	US 6100126 A	20000808	14	Method of making a resistor utilizing a polysilicon plug	438/238	438/151; 438/152;	4 4

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